

Topic :- SEMICONDUCTOR ELECTRONICS: MATERIALS, DEVICES AND SIMPLE CIRCUITS

1 (b)

$$\bar{A} \cdot \bar{A} = \bar{A} + \bar{\bar{A}} = \bar{A} + A = 1$$

$$A \cdot \bar{A} = 0$$

$$A + \bar{A} = 1$$

$$A + 1 = 1$$

2 (b)

The conductivity of an intrinsic semiconductor decreases with decrease in temperature and so it behaves as an insulator at 0 K. The conductivity of an insulator is zero. Therefore, the electrical conductivity of an intrinsic semiconductor at 0 K is equal to zero.

5 (c)

When a $p - n$ junction is formed, n -side attains positive potential and p -side attains negative. When ends of p and n of a $p - n$ junction are joined by a wire, there will be a steady conventional current from n -side to p -side through the wire and p -side to n -side through the $p - n$ junction.

6 (c)

Wood is non-crystalline

7 (c)

At ordinary temperature $n_e = n_h$.

8 (d)

As shown, we conclude that A and C are analogue signals but B is digital signal.

9 (b)

In reverse biasing, width of depletion layer increases

10 (c)

$$R_p = \frac{V_p}{i_p} = \frac{50}{150 \times 10^{-3}} = 333.3 \Omega$$

11 (b)

$$V_b - i_b R_b \Rightarrow R_b = \frac{9}{35 \times 10^{-6}} = 257 \text{ k}\Omega$$

12 (d)

In forward biasing both V_B and x decreases

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(a)

Truth table for given combination is

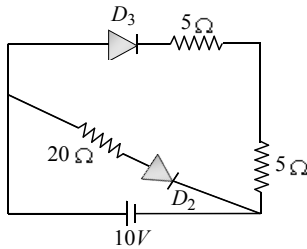
A	B	X
0	0	0
0	1	1
1	0	1
1	1	1

This comes out to be truth table of OR gate.

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(c)

In the given circuit, diode D_1 is reverse biased, so it will not conduct. Diodes D_2 and D_3 are forward biased, so they will conduct. The corresponding equivalent circuit is as shown in the figure



The equivalent resistance of the circuit is

$$R_{eq} = \frac{(5 + 5) \times 20}{(5 + 5) + 20} = \frac{10 \times 20}{10 + 20} = \frac{200}{30} = \frac{20}{3} \Omega$$

Current through the battery, $I = \frac{10V}{\frac{20}{3}\Omega} = 1.5A$

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(c)

If the voltage of the DC source is increased then both conductor and semiconductor registers same current i_e , semiconductor is in forward biased condition and it conducts. So, ammeters connected to both semiconductor and conductor will register the same current.

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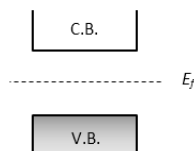
(b)

The temperature coefficient of resistance of silicon (i_e , semiconductor) is negative and that of platinum (i_e , conductor) is positive.

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(c)

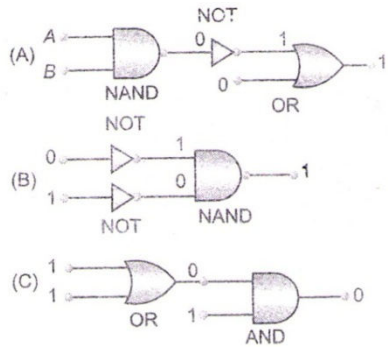
In forward biasing of PN junction diode width of depletion layer decreases. In intrinsic semiconductor fermi energy level is exactly in the middle of the forbidden gap



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(a)

The output gate circuit will be as shown below.



Hence, outputs of *A*, *B* and *C* are 1, 1, and 0 respectively.

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ANSWER-KEY										
Q.	1	2	3	4	5	6	7	8	9	10
A.	B	B	C	C	C	C	C	D	B	C
Q.	11	12	13	14	15	16	17	18	19	20
A.	B	D	A	C	D	C	B	C	C	A

PE